

## Supplementary Information

# Depth-Resolved Band Alignments of Perovskite Solar Cells with Significant Interfacial Effects

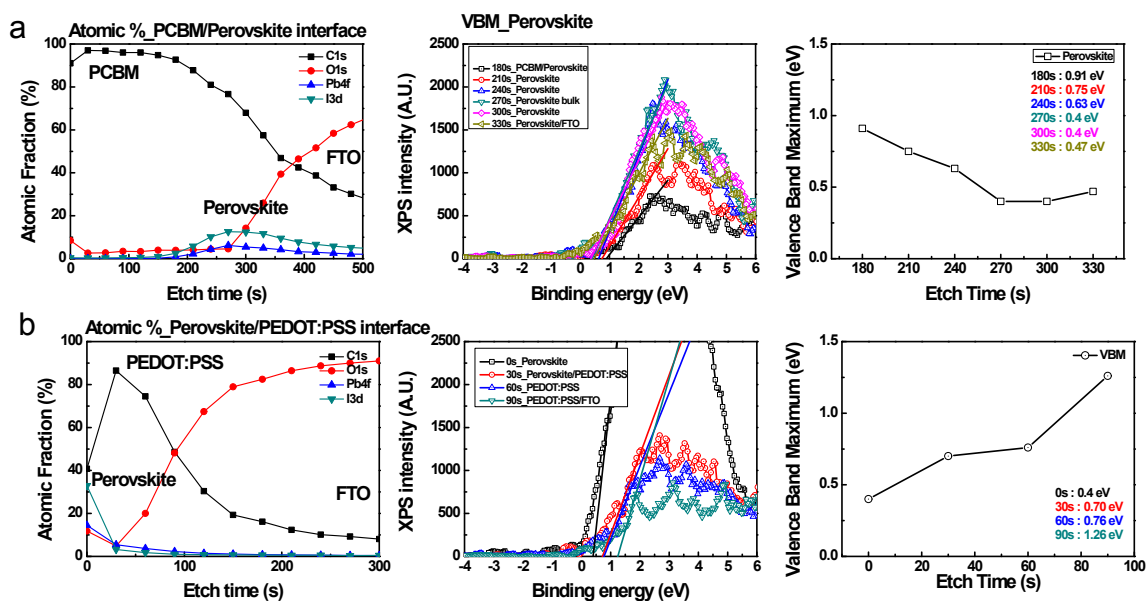
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### 1. VB maximum energies extracted from VB edge XPS spectra

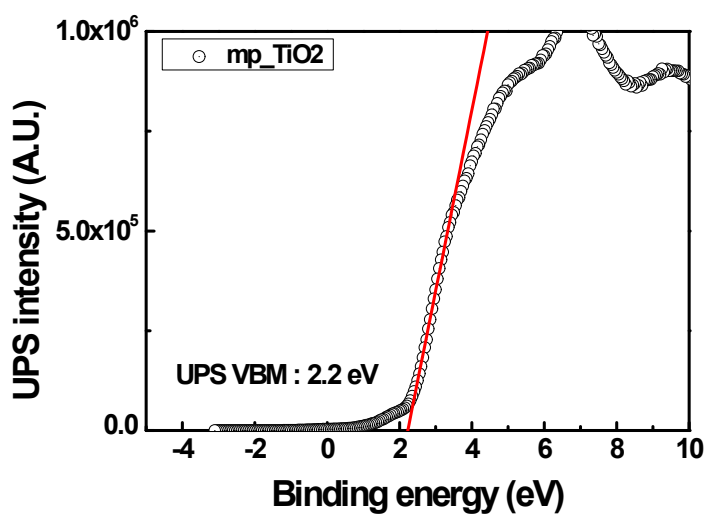
**Figure S1.** Atomic fraction (left), VB edge XPS spectra (middle), and VB maximum energies extracted from VB edge XPS spectra as a function of sputtering time (right) for (a) PCBM/perovskite and (b) perovskite/PEDOT:PSS interface.



## 2. UPS data of TiO<sub>2</sub> layer

The VB edge spectra of the UPS and XPS measurements of TiO<sub>2</sub> exhibit n-type characteristics with the Fermi energy level close to the CB minimum. In the UPS results (Figure S1.) for the mp-TiO<sub>2</sub> surface without Ar ion etching, the VBM was found to be 2.2 eV. Consequently, it was confirmed that the characteristics of typical n-type TiO<sub>2</sub> are deduced in combination with the bandgap of mp-TiO<sub>2</sub> (3.26 eV), as derived from a Tauc plot.

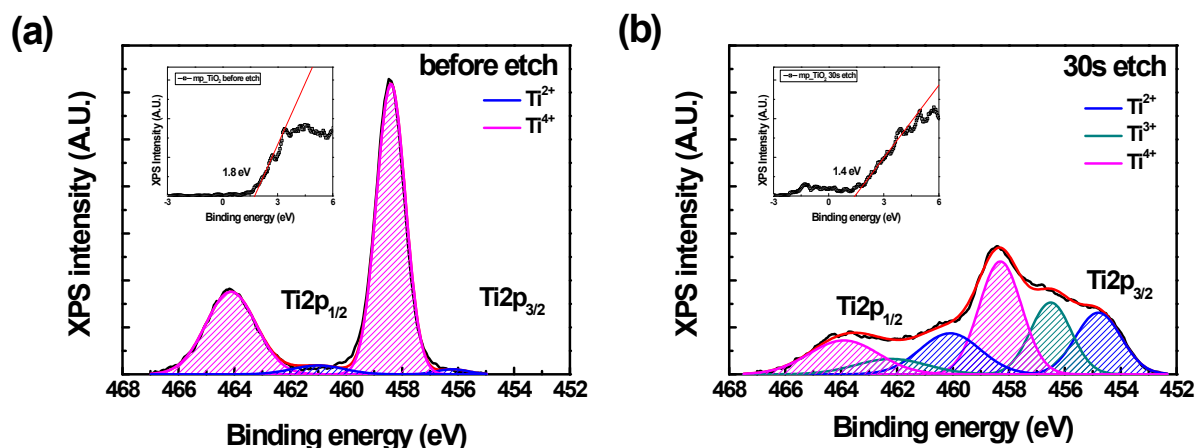
**Figure S2.** UPS data for mp-TiO<sub>2</sub> layer



### 3. XPS data of mp-TiO<sub>2</sub> before and after Ar ion sputtering

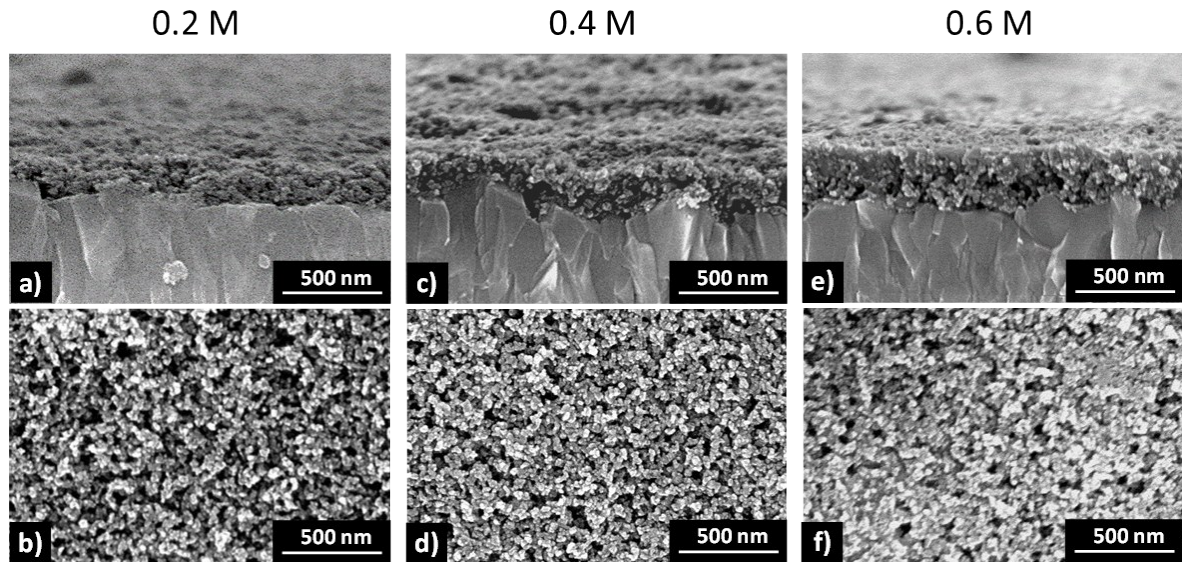
In Figure S2, the Ti2p XPS spectrum shows the Ti<sup>4+</sup> peak (Ti2p<sub>3/2</sub>: 458.4 eV, Ti2p<sub>1/2</sub>: 464.1 eV) dominant binding states before Ar ion sputtering, which is the typical chemical property of regular TiO<sub>2</sub>. The VBM value was also measured at 1.8 eV with n-type characteristics. However, after Ar ion sputtering for 30 s for 5- to 10-nm depth analysis from the top surface, the Ti2p spectrum revealed reduced TiO<sub>x</sub> bond characteristics with peak components of Ti<sup>2+</sup> (Ti2p<sub>3/2</sub>: 454.8 eV, Ti2p<sub>1/2</sub>: 460.1 eV), Ti<sup>3+</sup> (Ti2p<sub>3/2</sub>: 456.5 eV, Ti2p<sub>1/2</sub>: 462.1 eV). In addition, VBM was also slightly negative-shifted to 1.4 eV, while the high sub-VB edge states overlapped at 0 eV of the E<sub>F</sub> level. This is clear evidence of partially reduced TiO<sub>x</sub> as a result of the Ar-sputter-induced bond-breaking, since mp-TiO<sub>2</sub> has a porous structure, which preferentially loses O ions from the lattice as a result of Ar ion bombardment. Therefore, non-destructive XPS analysis should be performed for an mp-TiO<sub>2</sub>/perovskite interface.

Figure S3. XPS Ti2p narrow scan peak and VBM (a) before etch, (b) 30s Ar ion etched



#### 4. SEM images of samples with different perovskite concentration

**Figure S4.** Cross sectional and plane-view SEM images for perovskite (upper layer) cross sectional (lower layer) plane-view



#### 5. Average performances of PSCs

**Table S1.** Average solar cell parameters of planar and mesoporous (mp) structure PSCs

	$V_{oc}$ (V)	$J_{sc}$ (mA/cm <sup>2</sup> )	Fill Factor	PCE (%)
mp structure	$0.98 \pm 0.03$	$22.43 \pm 0.81$	$0.61 \pm 0.03$	$13.2 \pm 0.90$
planar structure	$0.89 \pm 0.04$	$18.48 \pm 0.48$	$0.68 \pm 0.03$	$11.2 \pm 0.67$

± represents standard deviation.